

# Myxa design notes

## Phase signal sensing

This document describes main decisions when designing Myxa PMSM controller.

Sections:

- MCU
- Step-down converter
- DRV8302
- Power mosfets
- Phase current sensing
- Phase signal sensing
- Input capacitor battery
- UAVCAN
- USB
- AUX input
- TVS diode

## MCU

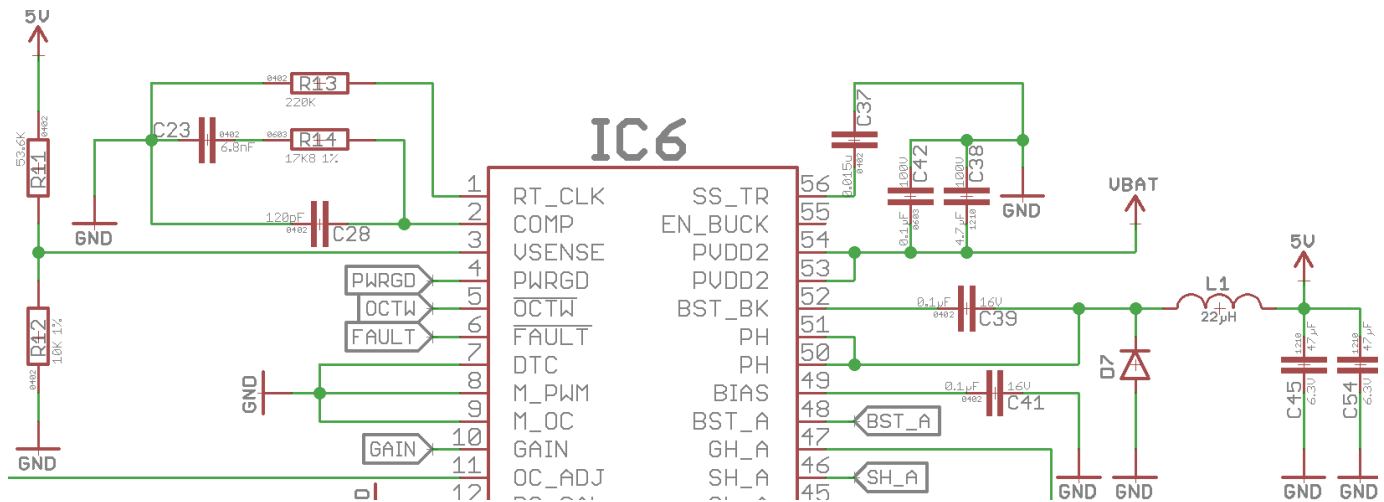
MYXA uses STM32F446 MCU, preferably with operating temperature range -40..+105C. Current boards though have only -40°C ~ 85°C MCU version. This is known issue and a least-evil solution due to the lack of proper MCUs in the world.

MCU is powered by dedicated [3.3V LDO](#).

VDDA is tied to reference voltage source [REF3033](#). It may seem weird, but it is capable of providing up to 25mA current, so its ok.

## Step-down converter

Step-down dc-dc converter is [tps54160](#) embedded in [DRV8302](#)



Inductor [SRP6540-220M](#) (FIXED IND 22UH 2.5A 133 MOHM SMD)

Shottky diode: [PMEG6020ER,115](#) (DIODE SCHOTTKY 60V 2A SOD123W)

**Input:**

Vin = 8..60V

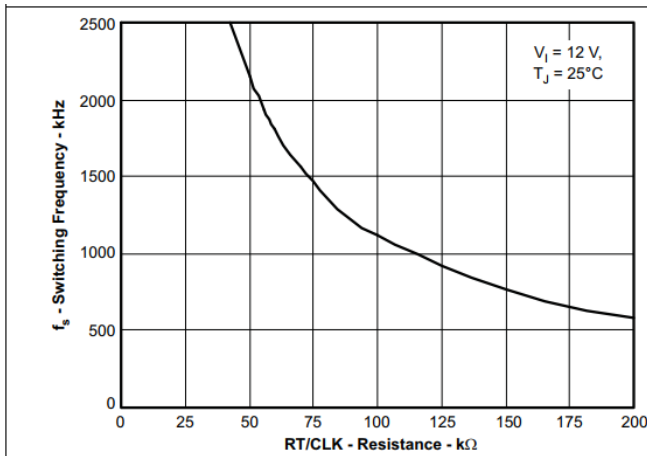
**Output:**

R1 = 10K, R2 = 53,6K

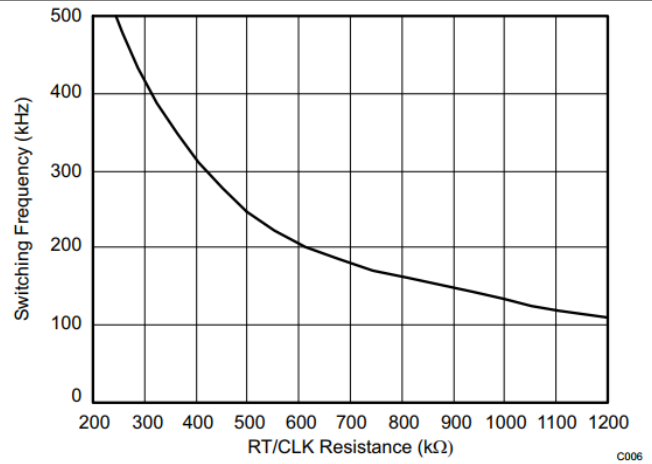
$$V_{out} = 53,6/10 * 0,8 + 0,8 = 5,088V$$

$I_{out} = 1.5A$  Max

### Operating frequency:



**Figure 6. Switching Frequency vs RT/CLK Resistance High Frequency Range**

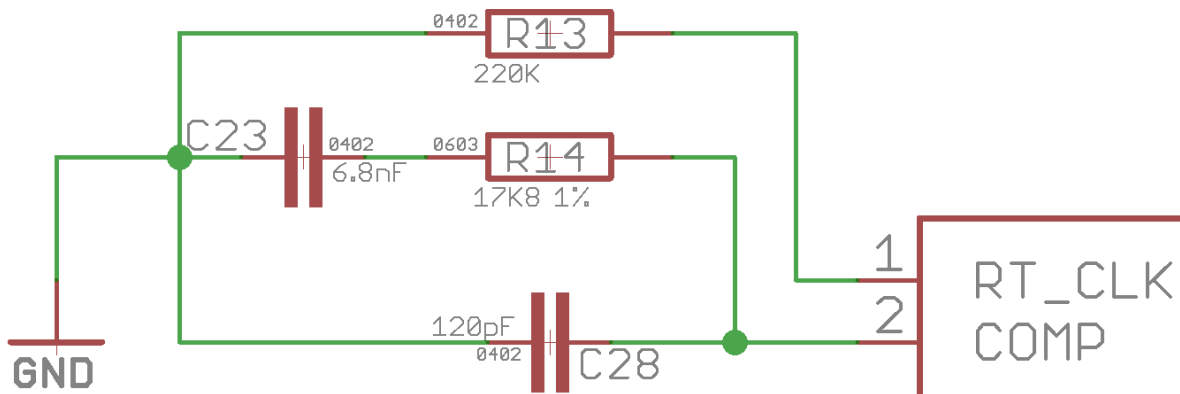


**Figure 7. Switching Frequency vs RT/CLK Resistance Low Frequency Range**

$R_{rt/clk} = 220K$

$F \sim 500$  KHz

### Compensation network



## DRV8302

DRV8302 schematic is basically its reference schematic from [datasheet](#)

One of the differences are capacitors on current shunt amplifiers outputs. In MYXA they are 18pF.

Pins EN\_GATE, PWRGD, OCTW, FAULT and GAIN are connected to MCU.

M\_PWM, M\_OC are set to LOW

DTC and DC\_CAL are tied to GND

DRV8302 Reference voltage input is connected to the same voltage as MCU V<sub>dda</sub>

Configuration pins description can be seen below:

### Pin Functions

PIN		I/O <sup>(1)</sup>	DESCRIPTION
NO.	NAME		
1	RT_CLK	I	Resistor timing and external clock for buck regulator. Resistor should connect to GND (PowerPAD™) with very short trace to reduce the potential clock jitter due to noise.
2	COMP	O	Buck error amplifier output and input to the output switch current comparator.
3	VSENSE	I	Buck output voltage sense pin. Inverting node of error amplifier.
4	PWRGD	I	An open drain output with external pullup resistor required. Asserts low if buck output voltage is low due to thermal shutdown, dropout, overvoltage, or EN_BUCK shut down
5	nOCTW	O	Overcurrent and overtemperature warning indicator. This output is open drain with external pullup resistor required.
6	nFAULT	O	Fault report indicator. This output is open drain with external pullup resistor required.
7	DTC	I	Dead-time adjustment with external resistor to GND
8	M_PWM	I	Mode selection pin for PWM input configuration. If M_PWM = LOW, the device supports 6 independent PWM inputs. When M_PWM = HIGH, the device must be connected to ONLY 3 PWM input signals on INH_x. The complementary PWM signals for low side signaling will be internally generated from the high side inputs.
9	M_OC	I	Mode selection pin for over-current protection options. If M_OC = LOW, the gate driver will operate in a cycle-by-cycle current limiting mode. If M_OC = HIGH, the gate driver will shutdown the channel which detected an over-current event.
10	GAIN	O	Gain selection for integrated current shunt amplifiers. If GAIN = LOW, the internal current shunt amplifiers have a gain of 10V/V. If GAIN = HIGH, the current shunt amplifiers have a gain of 40V/V.
11	OC_ADJ	I	Overcurrent trip set pin. Apply a voltage on this pin to set the trip point for the internal overcurrent protection circuitry. A voltage divider from DVDD is recommended.
12	DC_CAL	I	When DC_CAL is high, device shorts inputs of shunt amplifiers and disconnects loads. DC offset calibration can be done through external microcontroller.

### Overcurrent Protection (OCP)

#### 7.3.4.1 Overcurrent Protection (OCP) and Reporting

To protect the power stage from damage due to excessive currents, V<sub>DS</sub> sensing circuitry is implemented in the DRV8302. Based on the R<sub>DS(on)</sub> of the external MOSFETs and the maximum allowed I<sub>DS</sub>, a voltage threshold can be determined to trigger the overcurrent protection features when exceeded. The voltage threshold is programmed through the OC\_ADJ pin by applying an external reference voltage with a DAC or resistor divider from DVDD. Overcurrent protection should be used as a protection scheme only; it is not intended as a precise current regulation scheme. There can be up to a 20% tolerance across channels for the V<sub>DS</sub> trip point.

$$V_{DS} = I_{DS} \times R_{DS(on)} \quad (2)$$

The V<sub>DS</sub> sense circuit measures the voltage from the drain to the source of the external MOSFET while the MOSFET is enabled. The high-side sense is between the PVDD and SH\_X pins. The low-side sense is between the SH\_X and SL\_X pins. Ensuring a differential, low impedance connection to the external MOSFETs for these lines helps provide accurate V<sub>DS</sub> sensing.

There are two different overcurrent modes that can be set through the M\_OC pin.

##### 7.3.4.1.1 Current Limit Mode (M\_OC = LOW)

In current limit mode the devices uses current limiting instead of device shutdown during an overcurrent event. After the overcurrent event, the MOSFET in which the overcurrent was detected in will shut off until the next PWM cycle. The overcurrent event will be reported through the nOCTW pin. The nOCTW pin will be held low for a maximum 64 μs period (internal timer) or until the next PWM cycle. If another overcurrent event is triggered from another MOSFET, during a previous overcurrent event, the reporting will continue for another 64 μs period (internal timer will restart) or until both PWM signals cycle.

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#### 7.3.4.1.2 OC Latch Shutdown Mode

When an overcurrent event occurs, both the high-side and low-side MOSFETs will be disabled in the corresponding half-bridge. The nFAULT pin will latch until the fault is reset through a quick EN\_GATE reset pulse.

#### 7.3.4.2 OC\_ADJ

When external MOSFET is turned on, the output current flows through the on resistance,  $R_{DS(on)}$  of the MOSFET, which creates a voltage drop  $V_{DS}$ . The over current protection event will be enabled when the  $V_{DS}$  exceeds a pre-set value. The voltage on OC\_ADJ pin will be used to pre-set the OC tripped value. The OC tripped value  $I_{OC}$  has to meet following equations:

$$\frac{R2}{(R1 + R2)} \times DVDD = V_{DS}$$

where

- $R1 + R2 \geq 1 \text{ K}\Omega$
- $DVDD = 3.3 \text{ V}$

(3)

$$I_{OC} = \frac{V_{DS}}{R_{DS(on)}}$$

(4)

Connect OC\_ADJ pin to DVDD to disable the over-current protection feature.

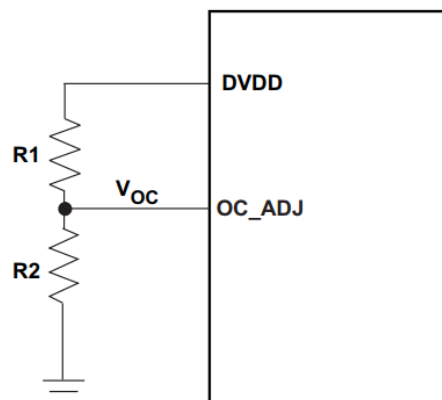


Figure 5. OC\_ADJ Current Programming Pin Connection

In current MYXA design

$R1 = 10\text{K}$

$R2 = 1.3\text{K}$

$DVDD = 3.3\text{V}$

$V_{ds} = 1.3 / (10 + 1.3) * 3.3 = 0.38$

$V_{ds} = 0.005 * I$ ,

$I_{trip} = 0.38 / 0.005 = 76\text{A}$

As power keys MYXA uses state of the art mosfets [BSC040N08NS5ATMA1](#) (MOSFET N-CH 80V 100A 8TDFN) from Infineon Technologies

Brief description

FET Type	N-Channel	
Technology	MOSFET (Metal Oxide)	
Drain to Source Voltage (Vdss)	80V	
Current - Continuous Drain (Id) @ 25°C	100A (Tc)	
Drive Voltage (Max Rds On, Min Rds On)	6V, 10V	
Vgs(th) (Max) @ Id	3.8V @ 67µA	
Gate Charge (Qg) (Max) @ Vgs	54nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds	3900pF @ 40V	
Vgs (Max)	±20V	
FET Feature	-	
Power Dissipation (Max)	2.5W (Ta), 104W (Tc)	
Rds On (Max) @ Id, Vgs	4 mOhm @ 50A, 10V	
Operating Temperature	-55°C ~ 150°C (TJ)	
Mounting Type	Surface Mount	
Supplier Device Package	PG-TDFN-8	
Package / Case	8-PowerTDFN	

Each mosfet has 4R3 gate resistor to eliminate gate-ringing

Loss estimation at 12S@30A:

Static loss:

$P = (I^2 \cdot R) = 0.004 \cdot 30 \cdot 30 = 3,6 \text{ W}$

Dynamic loss:

$P = 1/2 \cdot V_{in} \cdot I_{out} \cdot (T_{rise} + T_{fall}) \cdot F_{switch}$

According to DRV8302 [datasheet](#)

6.6 Gate Timing and Protection Characteristics

			MIN	NOM	MAX	UNIT
TIMING, OUTPUT PINS						
t <sub>pd,lf-O</sub>	Positive input falling to GH_x falling	CL=1 nF, 50% to 50%		45		ns
t <sub>pd,lr-O</sub>	Positive input rising to GL_x falling	CL=1 nF, 50% to 50%		45		ns
T <sub>d_min</sub>	Minimum dead time after hand shaking <sup>(1)</sup>				50	ns
T <sub>dtp</sub>	Dead Time	With R <sub>DTC</sub> set to different values	50		500	ns
t <sub>GDr</sub>	Rise time, gate drive output	CL=1 nF, 10% to 90%		25		ns
t <sub>GDF</sub>	Fall time, gate drive output	CL=1 nF, 90% to 10%		25		ns

$T_{rise} = T_{fall} \sim 100 \text{ ns}$

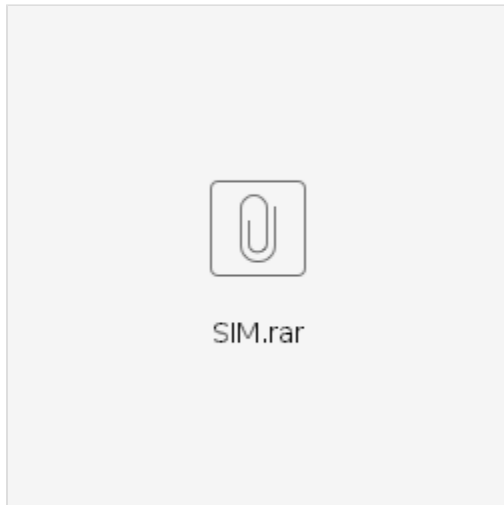
$P = 1/2 \cdot 50,4 \cdot 30 \cdot (100 + 100) \cdot 10^{-9} \cdot 45\,000 \sim 6,8 \text{ W}$

Total loss per switch Ploss\_sw ~ 11W

Total loss per phase Ploss\_ph ~ 22W

A [spreadsheet for calculations above](#)

Also simulation models to find out tRise and tFall times more precisely can be found below. It should be opened with LTSpice



## Phase current sensing

Current is sensed on two phases using [CSNL2512FT3L00](#) (RES SMD 0.003 OHM 1% 2W 2512) current shunts and current sense amplifiers integrated in DRV8302. Each current shunt has 1000pF capacitor connected across it.

Current shunt amplifier gain can be either 10 or 40x depending on GAIN pin of DRV8302 which is controlled by the MCU.

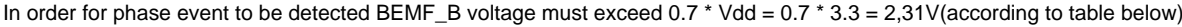
This gives maximum measurable current

$I_{max} = 3.3 / (10 * 0.003) = 110A$  for 10x gain. But max differential voltage of current amplifier is 300mV, so  $I_{max} = 0.3 / 0.003 = 100A$

$I_{max} = 3.3 / (40 * 0.003) = 27.5A$  for 40x gain

## Phase signal sensing

Instead of more conventional analog voltage reading for phase signal MYXA uses different approach. It monitors signal transition from 0 to 1 on MCU pin, where phase signal is connected to. For that purpose resistor divider for each phase signal is implemented. One of them can be seen below:



In order for phase event to be detected BEMF\_B voltage must exceed  $0.7 \cdot V_{dd} = 0.7 \cdot 3.3 = 2,31V$  (according to table below)

**Table 56. I/O static characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>IL</sub>	FT, FTf, TTa and NRST I/O input low level voltage	1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	-	-	0.35V <sub>DD</sub> - 0.04 <sup>(1)</sup>	V
					0.3V <sub>DD</sub> <sup>(2)</sup>	
	BOOT0 I/O input low level voltage	1.75 V ≤ V <sub>DD</sub> ≤ 3.6 V, - 40 °C ≤ T <sub>A</sub> ≤ 105 °C	-	-	0.1V <sub>DD</sub> + 0.1 <sup>(1)</sup>	
		1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V, 0 °C ≤ T <sub>A</sub> ≤ 105 °C	-	-		
V <sub>IH</sub>	FT, FTf, TTa and NRST I/O input high level voltage <sup>(4)</sup>	1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	0.45V <sub>DD</sub> + 0.3 <sup>(1)</sup>	-	-	V
			0.7V <sub>DD</sub> <sup>(2)</sup>			
	BOOT0 I/O input high level voltage	1.75 V ≤ V <sub>DD</sub> ≤ 3.6 V, - 40 °C ≤ T <sub>A</sub> ≤ 105 °C	0.17V <sub>DD</sub> + 0.7 <sup>(1)</sup>	-	-	
	1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V, 0 °C ≤ T <sub>A</sub> ≤ 105 °C					
V <sub>HYS</sub>	FT, FTf, TTa and NRST I/O input hysteresis	1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	-	10%V <sub>DD</sub>	-	V
	BOOT0 I/O input hysteresis	1.75 V ≤ V <sub>DD</sub> ≤ 3.6 V, -40 °C ≤ T <sub>A</sub> ≤ 105 °C	-	100m	-	
			1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V, 0 °C ≤ T <sub>A</sub> ≤ 105 °C		-	
I <sub>lkg</sub>	I/O input leakage current <sup>(3)</sup>	V <sub>SS</sub> ≤ V <sub>IN</sub> ≤ V <sub>DD</sub>	-	-	±1	μA
	I/O FT input leakage current <sup>(4)</sup>	V <sub>IN</sub> = 5 V	-	-	3	

So, with resistor divider of 17K8 and 5K1 this will happen when phase B voltage will be

$$3,3 * 0,7 / (5,1/17,8 + 5,1) \sim 10,3\text{ V}$$

## Input capacitor battery

Main input capacitor is [820uF 80V aluminum cap](#), which is placed as near to power mosfets as possible. Also at least two low-esr [4.7uF 100V](#) caps are added per phase.

## UAVCAN

MYXA has two UAVCAN interfaces. MYXA can provide UAVCAN with 5V power source through controllable Current Switch Regulator [TPD3S014 DBVR](#), which can also act as e-fuse limiting UAVCAN current to 500mA

Both UAVCAN interfaces use [TJA1051TK/3,118](#) (IC TXRX CAN HIGH SPEED 8HVSON) driver chips, which are supplied with 5V line and IO line is connected to 3.3V.

## USB

USB consists of only one [microUSB connector](#) and miniature USB-specific [TVS-diode array](#)

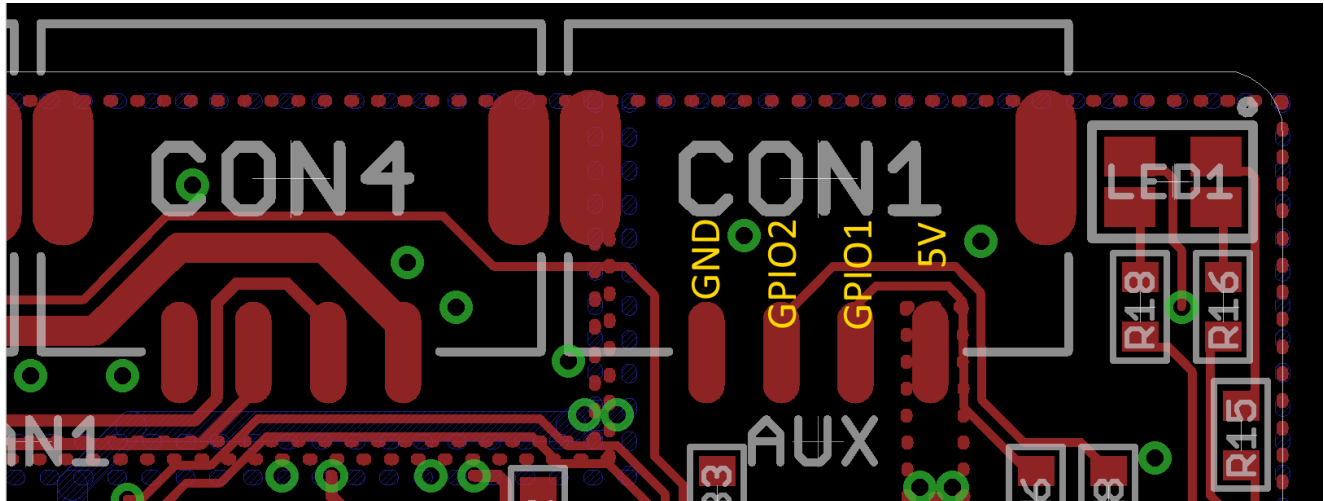


MYXA can be powered via USB(Obviously without powerstage), as USB Vdd is connected to 5V line with [CRS08](#) Schottky diode

There are also footprints for serial resistors for D+ and D- lines in case some more protection needed. As for now they are replaced with 0 ohm resistors.

## AUX input

MYXA has two AUX inputs which are routed to [UAVCAN-like 4-pin](#) connector. This connector can provide 5V power to external circuitry as well. 5V AUX line current consumption is limited with [resettable fuse](#) (PTC RESTTBLE 0.50A 16V CHIP 1210) and one of UAVCAN Current Switch Regulators.



Both AUX inputs are protected with [diode half-bridge](#)

GPIO2 is routed directly to the output connector and can be found on pin PA4(ADC3\_IN4) of MCU.

GPIO1 is routed to PA3(ADC3\_IN3) pin of MCU and also to PB14 pin(where TIM12\_CH1 can be found). It is also connected to PC4 with 1K series resistor, so it can be used to connect NTC or PTC thermistor with typical resistance of about 1K(like [this one](#)). The thermistor should be connected between GND and GPIO1 pins of the AUX connector. Then PC5 should activate PULL-UP to 3.3V and form a resistor divider with 1K resistor(between 3.3v and measured voltage) and thermistor(between measured voltage and gnd) and GPIO1(ADC3\_IN3) may be measured.

Also digital 1wire thermometers(like [ds18b20](#)) may be used on GPIO1 using PWM generation on TIM12\_CH1 and DMA to guarantee proper 1-wire timings. This may come handy in extremely noisy environments when analog readings on long thermistor wires are corrupted

## TVS diode

Although by default Myxa is shipped without TVS diode installed, there may be some situations that require it installed. In that case user can install it by himself on the provided footprint. The best choice is [SMBJ54A](#) from Littlefuse although any other TVS diode in DO214AA package and with breakdown voltage no more than 60V will fit.

The footprint for the diode is shown on the picture below

